

Green Products

SB5200 SCHOTTKY RECTIFIER

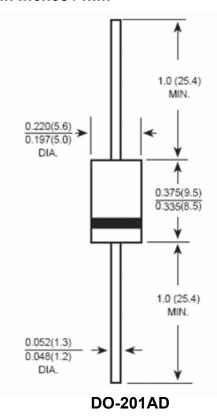
Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

Features:

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In Inches / mm



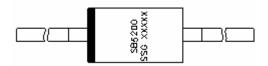
[•] Weigi Street, Airport Development Zone, Jiangning District, Nanjing, China 211113 📱 (86) 25-87123907 •

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Marking Diagram:



Where XXXXX is YYWWL

 SB
 = Device Type

 5
 = Forward Current (5A)

 200
 = Reverse Voltage (200V)

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
SB5200	DO-201AD	1250 pcs / tape
	(Pb-Free)	1250 pcs / tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

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Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

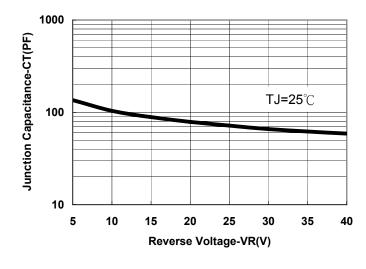
Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	SB5200	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	200	V
Average Rectified Output Current (Note 1) @T _A = -	I05°C	5.0	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	120	А
Forward Voltage $@I_F = 5.0A, T_A$ $@I_F = 5.0A, T_A$	= 25°C = 125°C	1.10 0.90	V
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	25°C I _{RM}	1 7	mA
Typical Thermal Resistance Junction to Ambien	t R _{θJA}	10	°C /W
Storage Temperature Range	T _{STG}	-55 to +150	°C
Max. Junction Temperature	T _J	-55 to +150	°C
Case Style		DO-201AD	

Note:1. Leads maintained at ambient temperature at a distance of 9.5mm from the case.

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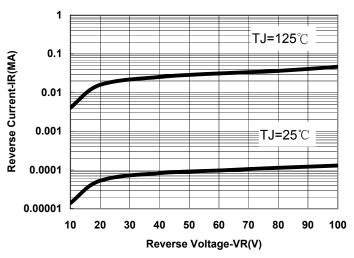


Fig.1-Typical Junction Capacitance

Fig.2-Typical Values Of Reverse Current

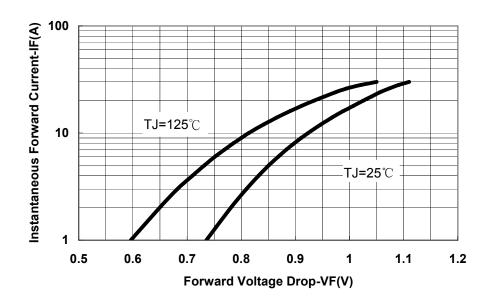


Fig.3-Typical Forward Voltage Drop Characteristics

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